

## isc Silicon PNP Power Transistor

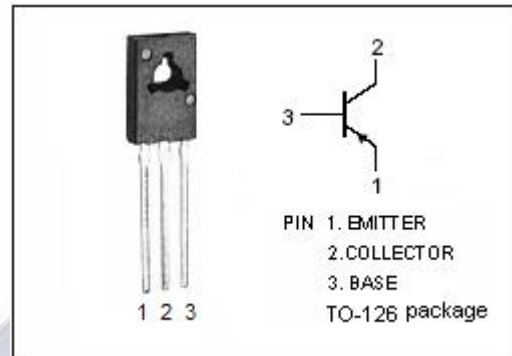
## 2SA1358

### DESCRIPTION

- High Collector-Emitter Breakdown Voltage  
:  $V_{(BR)CEO} = -120V(\text{Min})$
- Complement to Type 2SC3421
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

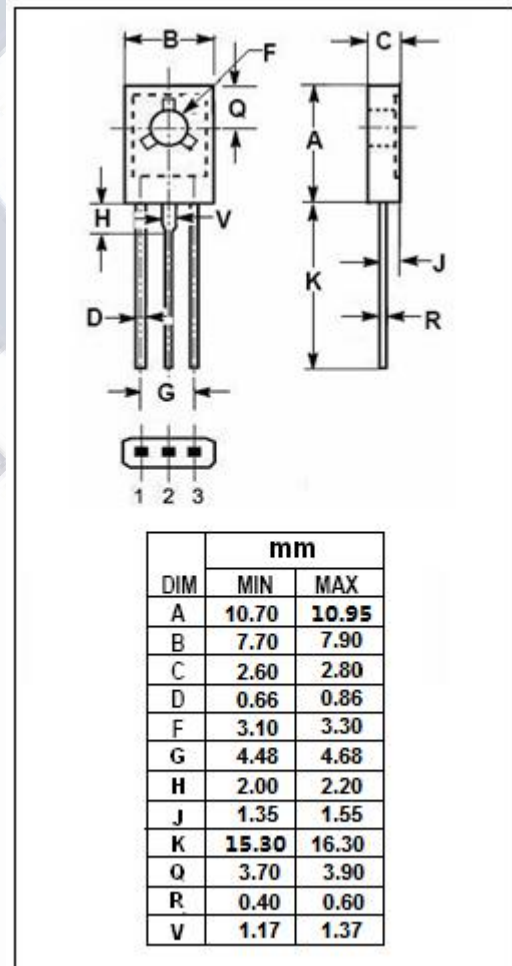
### APPLICATIONS

- Designed for audio frequency power amplifier applications.



### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-120	V
$V_{CEO}$	Collector-Emitter Voltage	-120	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-1	A
$I_B$	Base Current-Continuous	-0.1	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	10	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.5	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon PNP Power Transistor****2SA1358****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}$ ; $I_B = 0$	-120			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -1\text{mA}$ ; $I_C = 0$	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -500\text{mA}$ ; $I_B = -50\text{mA}$			-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -500\text{mA}$ ; $V_{CE} = -5\text{V}$			-1.0	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -120\text{V}$ ; $I_E = 0$			-0.1	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{V}$ ; $I_C = 0$			-0.1	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = -0.1\text{A}$ ; $V_{CE} = -5\text{V}$	80		240	
$f_T$	Current-Gain—Bandwidth Product	$I_C = -0.1\text{A}$ ; $V_{CE} = -5\text{V}$		120		MHz
$C_{OB}$	Output Capacitance	$I_E = 0$ ; $V_{CB} = -10\text{V}$ , $f_{test} = 1\text{MHz}$		30		pF

◆  **$h_{FE}$  Classifications**

O	Y
80-160	120-240